No. M15-vi $Cd_{1-x}Zn_xTe$

1a	Ferroelectricity in $Cd_{1-x}Zn_xTe$ (x = 0.04...0.45) was found from the dielectric constant and *D–E* hysteresis loop by R. Weil et al. in 1989.			89Wei
b	phase	II	I	
	state	F [a])	P [a])	[a]) 89Wei
	crystal system	rhombohedral [b])	cubic [c])	[b]) 90Mar, 91Nku [c]) 91Nku
	Transition temperature varies from 100 °C to 250 °C with composition x.			89Wei, 93Ter
	Polar axis || [111].			89Wei, 90Mar
2	Crystal growth: modified Bridgman method: see			83Mur
3a	Unit cell parameters: a = 6.401(1) Å, α = 89.94(1)° (rhombohedral) at RT for x = 0.22; see also Table M15-vi-001.			90Mar
b	Crystal structure: phase I, zinc blende (f.c.c.) structure; phase II, distorted zinc blende structure. The Te atom shifts by about 0.1 Å along a ⟨111⟩ direction from the original position in a true zinc blende structure. Table M15-vi-001.			91Nku 90Mar, 91Nku
5a	Dielectric constant vs. *T*: Fig. M15-vi-001, Fig. M15-vi-002. Curie constant and Curie temperature vs. x: Fig. M15-vi-003. Dielectric constant at optical frequency: see κ_∞ (x) = 7.26–0.05x.			93Ada1 93Ada2
c	*D–E* hysteresis loops: see P_s vs. *T* curve: Fig. M15-vi-004.			89Wei
6a	Heat capacity: see			93Ben, 98Kaw
9a	Refractive indices: Fig. M15-vi-005. Birefringence vs. *T*: Fig. M15-vi-006. Optical absorption and reflection: see Far-infrared reflectivity: see			93Ada1 93Tal
10a	Raman scattering: see			93Tal
11	Conductivity: $\sigma \approx 10^{-1}\Omega^{-1}m^{-1}$ at RT for x = 0.1. Charge-carrier mobilities for x = 0.2: electron mobility $\propto T^{-1.1}$ in 200...320 K (0.135 $m^2 V^{-1} s^{-1}$ at RT), hole mobility $\propto T^{-2.0}$ in 200...320 K (0.0120 $m^2 V^{-1} s^{-1}$ at RT). Photoluminescence spectra: see			93Ben 93Bur 93Dav
14c	EXAFS: see			93Bun, 93Ter